

# **Lecture 9: Combinational Circuit Design**

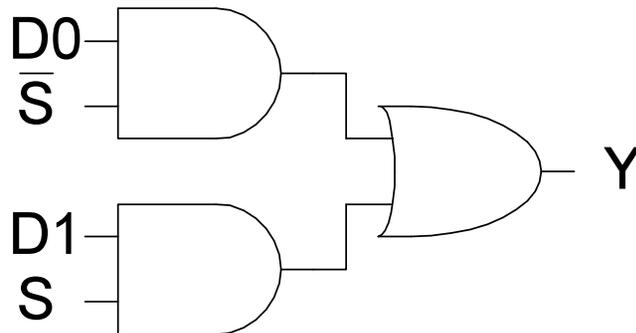
# Outline

- Bubble Pushing
- Compound Gates
- Logical Effort Example
- Input Ordering
- Asymmetric Gates
- Skewed Gates
- Best P/N ratio

# Example 1

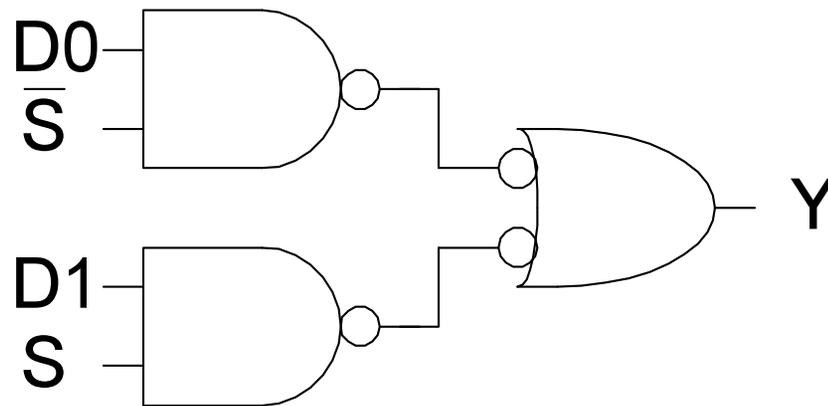
```
module mux(input s, d0, d1,  
           output y);  
  
    assign y = s ? d1 : d0;  
endmodule
```

1) Sketch a design using AND, OR, and NOT gates.



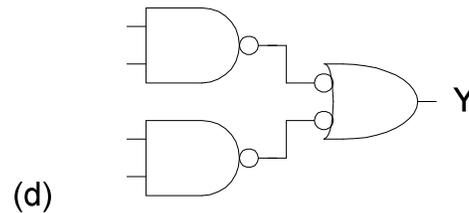
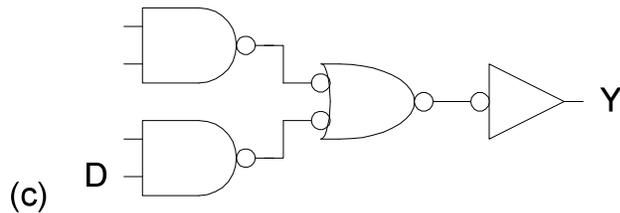
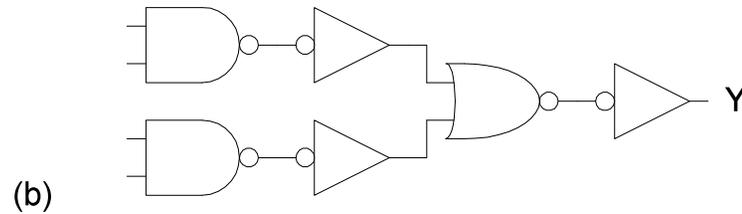
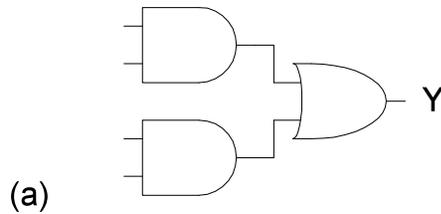
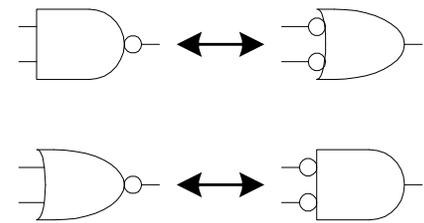
# Example 2

2) Sketch a design using NAND, NOR, and NOT gates.  
Assume  $\sim S$  is available.



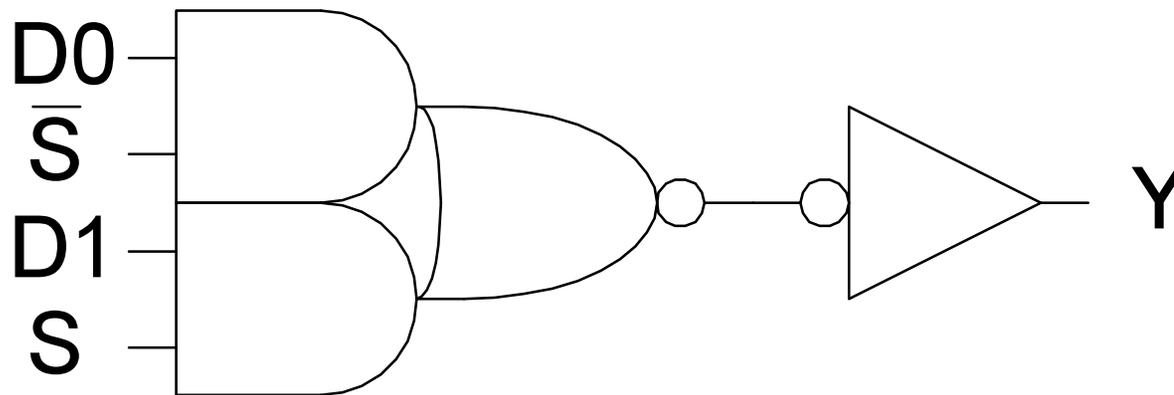
# Bubble Pushing

- ❑ Start with network of AND / OR gates
- ❑ Convert to NAND / NOR + inverters
- ❑ Push bubbles around to simplify logic
  - Remember DeMorgan's Law



# Example 3

3) Sketch a design using one compound gate and one NOT gate. Assume  $\sim S$  is available.

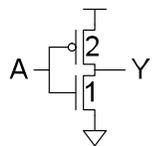
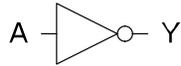


# Compound Gates

## □ Logical Effort of compound gates

unit inverter

$$Y = \overline{A}$$

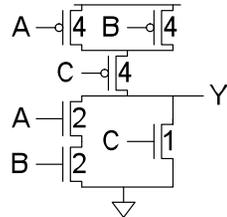
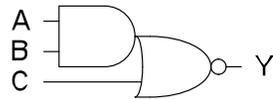


$$g_A = 3/3$$

$$p = 3/3$$

AOI21

$$Y = \overline{A \cdot B + C}$$



$$g_A = 6/3$$

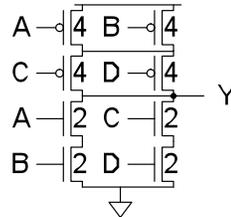
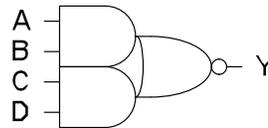
$$g_B = 6/3$$

$$g_C = 5/3$$

$$p = 7/3$$

AOI22

$$Y = \overline{A \cdot B + C \cdot D}$$



$$g_A =$$

$$g_B =$$

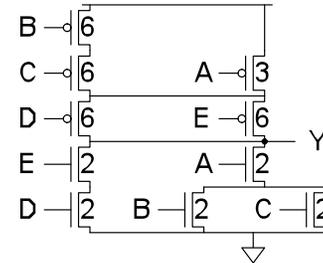
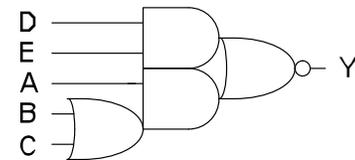
$$g_C =$$

$$g_D =$$

$$p =$$

Complex AOI

$$Y = \overline{A \cdot (B + C) + D \cdot E}$$



$$g_A =$$

$$g_B =$$

$$g_C =$$

$$g_D =$$

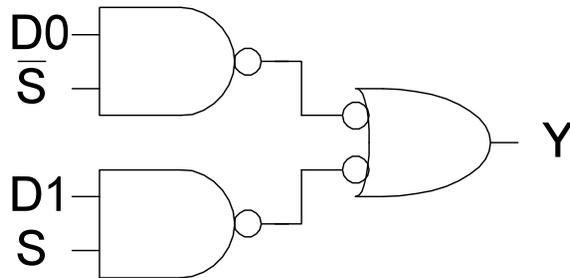
$$g_E =$$

$$p =$$

# Example 4

- The multiplexer has a maximum input capacitance of 16 units on each input. It must drive a load of 160 units. Estimate the delay of the two designs.

H =



$P =$

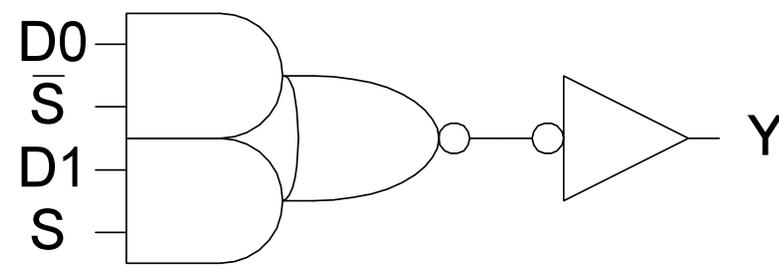
$G =$

$F =$

$\hat{f} =$

$D =$

B = N =



$P =$

$G =$

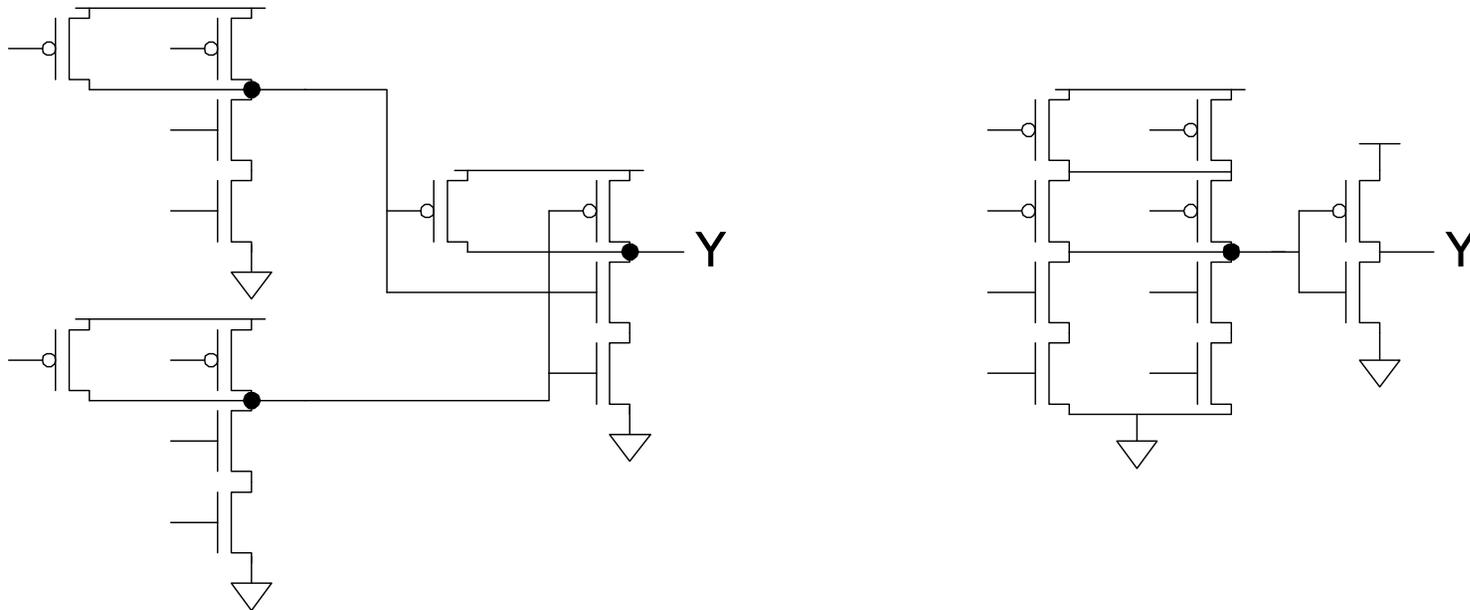
$F =$

$\hat{f} =$

$D =$

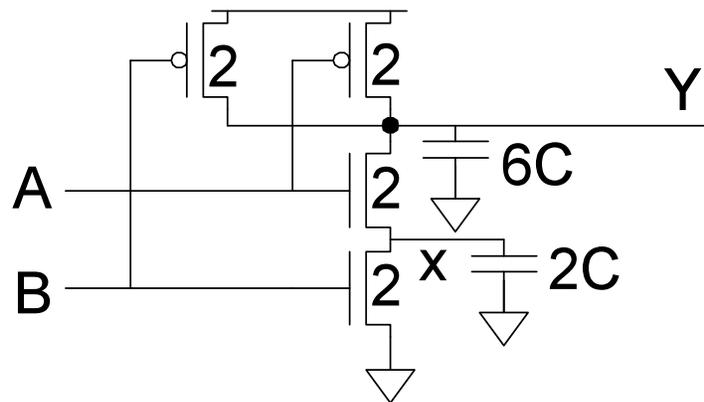
# Example 5

- Annotate your designs with transistor sizes that achieve this delay.



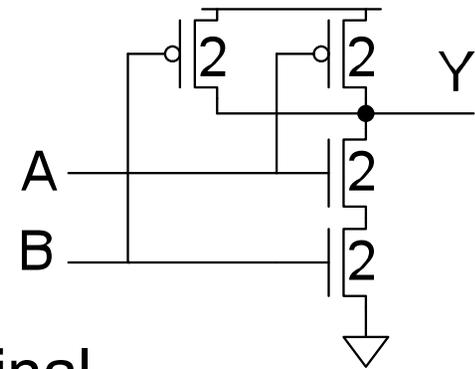
# Input Order

- ❑ Our parasitic delay model was too simple
  - Calculate parasitic delay for Y falling
    - If A arrives latest?
    - If B arrives latest?



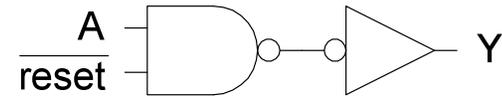
# Inner & Outer Inputs

- ❑ *Inner* input is closest to output (A)
- ❑ *Outer* input is closest to rail (B)
- ❑ If input arrival time is known
  - Connect latest input to inner terminal

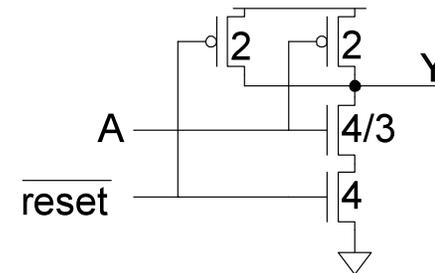


# Asymmetric Gates

- ❑ Asymmetric gates favor one input over another
- ❑ Ex: suppose input A of a NAND gate is most critical
  - Use smaller transistor on A (less capacitance)
  - Boost size of noncritical input
  - So total resistance is same

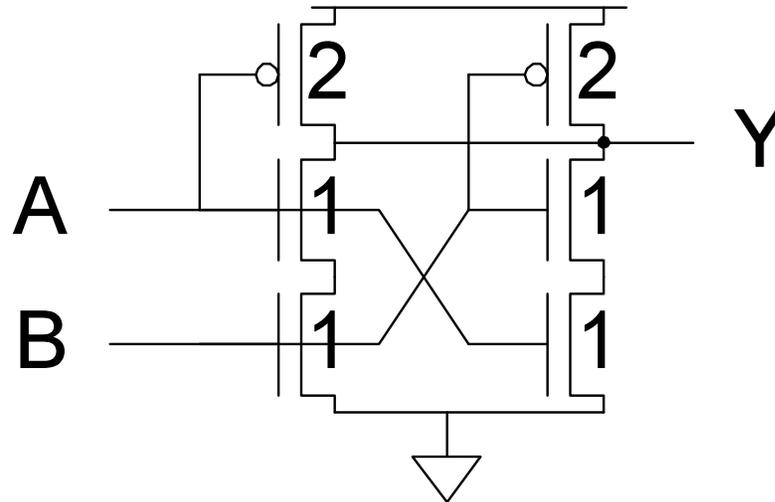


- ❑  $g_A =$
- ❑  $g_B =$  –
- ❑  $g_{\text{total}} = g_A + g_B =$
- ❑ Asymmetric gate approaches  $g = 1$  on critical input
- ❑ But total logical effort goes up



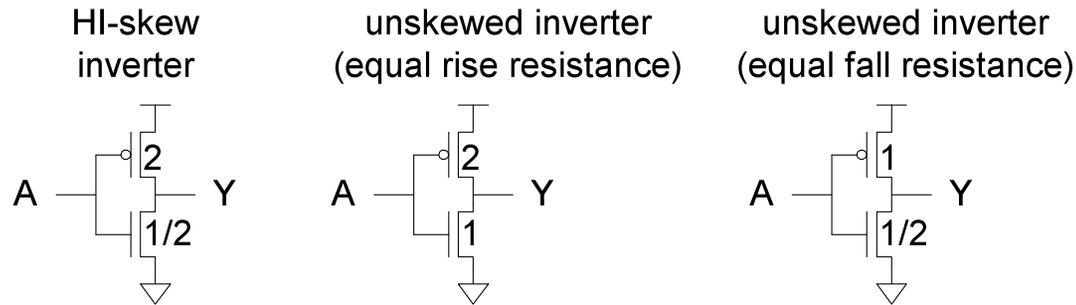
# Symmetric Gates

- Inputs can be made perfectly symmetric



# Skewed Gates

- ❑ Skewed gates favor one edge over another
- ❑ Ex: suppose rising output of inverter is most critical
  - Downsize noncritical nMOS transistor

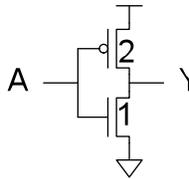
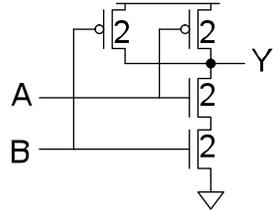
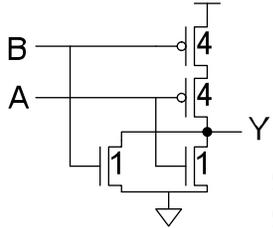
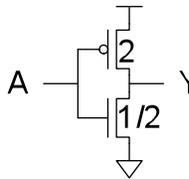
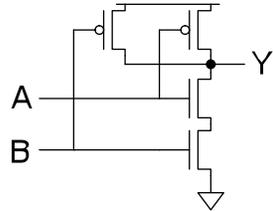
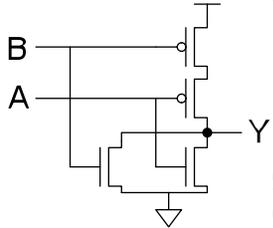
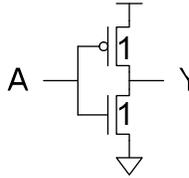
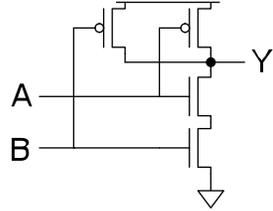
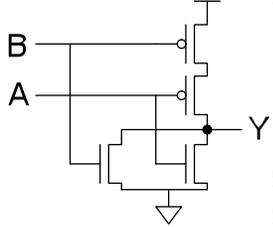


- ❑ Calculate logical effort by comparing to unskewed inverter with same effective resistance on that edge.
  - $g_u =$
  - $g_d =$

# HI- and LO-Skew

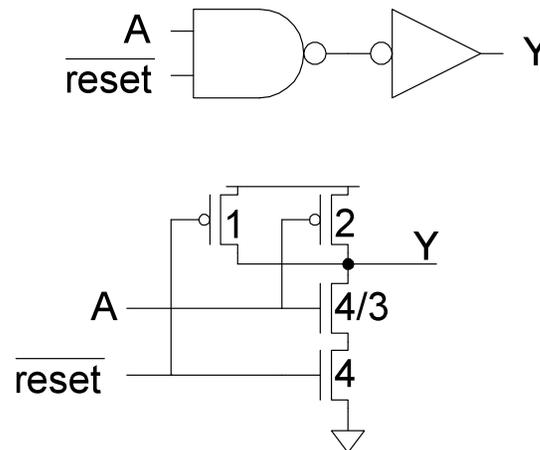
- ❑ Def: Logical effort of a skewed gate for a particular transition is the ratio of the input capacitance of that gate to the input capacitance of an unskewed inverter delivering the same output current for the same transition.
  
- ❑ Skewed gates reduce size of noncritical transistors
  - HI-skew gates favor rising output (small nMOS)
  - LO-skew gates favor falling output (small pMOS)
- ❑ Logical effort is smaller for favored direction
- ❑ But larger for the other direction

# Catalog of Skewed Gates

	Inverter	NAND2	NOR2
unskewed	 $g_u = 1$ $g_d = 1$ $g_{avg} = 1$	 $g_u = 4/3$ $g_d = 4/3$ $g_{avg} = 4/3$	 $g_u = 5/3$ $g_d = 5/3$ $g_{avg} = 5/3$
HI-skew	 $g_u = 5/6$ $g_d = 5/3$ $g_{avg} = 5/4$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$
LO-skew	 $g_u = 4/3$ $g_d = 2/3$ $g_{avg} = 1$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$

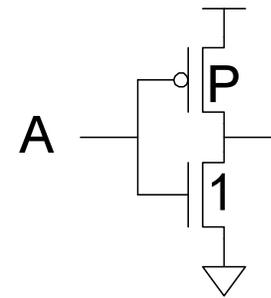
# Asymmetric Skew

- ❑ Combine asymmetric and skewed gates
  - Downsize noncritical transistor on unimportant input
  - Reduces parasitic delay for critical input



# Best P/N Ratio

- ❑ We have selected P/N ratio for unit rise and fall resistance ( $\mu = 2-3$  for an inverter).
- ❑ Alternative: choose ratio for least average delay
- ❑ Ex: inverter
  - Delay driving identical inverter
  - $t_{pdf} =$
  - $t_{pdr} =$
  - $t_{pd} =$
  - $dt_{pd} / dP =$
  - Least delay for  $P =$

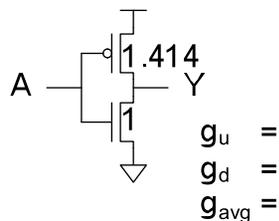


# P/N Ratios

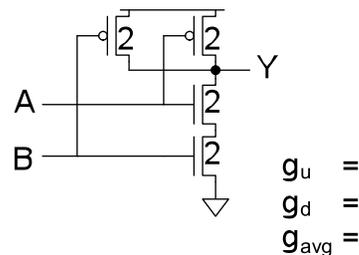
- In general, best P/N ratio is sqrt of equal delay ratio.
  - Only improves average delay slightly for inverters
  - But significantly decreases area and power

fastest  
P/N ratio

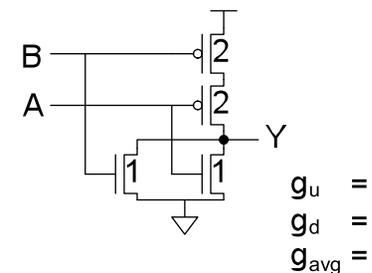
Inverter



NAND2



NOR2



# Observations

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- ❑ For speed:
  - NAND vs. NOR
  - Many simple stages vs. fewer high fan-in stages
  - Latest-arriving input
- ❑ For area and power:
  - Many simple stages vs. fewer high fan-in stages